

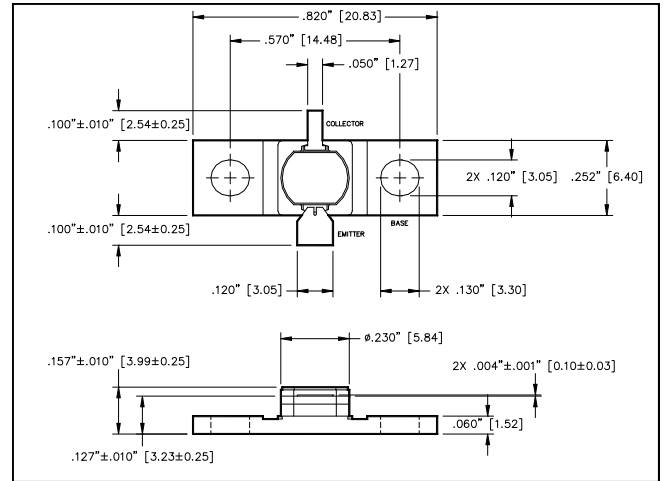
Features

- NPN silicon microwave power transistor
- Common base configuration
- Class C operation
- Interdigitated geometry
- Diffused emitter ballasting resistors
- Gold metalization system
- Hermetic metal/Ceramic package

ABSOLUTE MAXIMUM RATING AT 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V_{CES}	60	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Collector Current	I_C	0.2	A
Power Dissipation	P_D	7.0	W
Junction Temperature	T_J	200	°C
Storage Temperature	T_{STG}	-65 to +200	°C
Thermal Resistance	θ_{JC}	25	°C/W

Outline Drawing



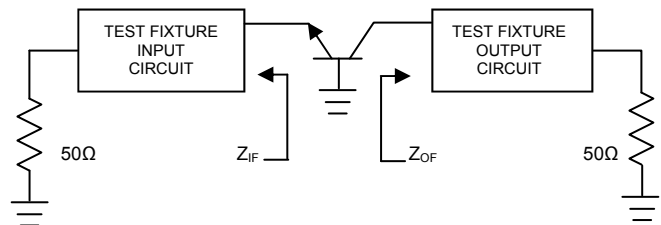
UNLESS OTHERWISE NOTED, TOLERANCES ARE INCHES ±.005" [MILLIMETERS ±0.13MM]

ELECTRICAL SPECIFICATIONS AT 25°C

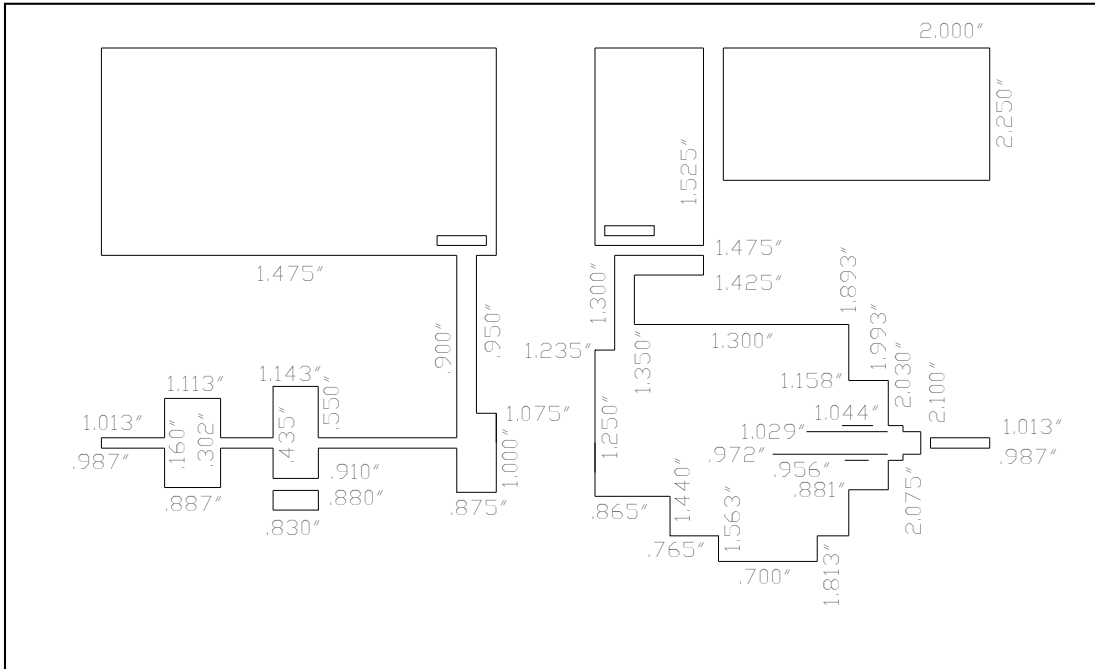
Parameter	Symbol	Min	Max	Units	Test Conditions
Collector-Emitter Breakdown Voltage	BV_{CES}	60	-	V	$I_C = 2.5\text{mA}$
Collector-Emitter Leakage Current	I_{CES}	-	0.5	mA	$V_{CE} = 28\text{V}$
Input Power	h_{FE}	-	0.158	w	$V_{CE} = 28\text{V}$, $P_{out} = 1.0\text{W}$, $F = 2.3\text{GHz}$
Power Gain	G_P	8	-	dB	$V_{CE} = 28\text{V}$, $P_{out} = 1.0\text{W}$, $F = 2.3\text{GHz}$
Collector Efficiency	η_C	30	-	%	$V_{CE} = 28\text{V}$, $P_{out} = 1.0\text{W}$, $F = 2.3\text{GHz}$
Input Return Loss	RL	6	-	dB	$V_{CE} = 28\text{V}$, $P_{out} = 1.0\text{W}$, $F = 2.3\text{GHz}$
Load Mismatch Tolerance	VSWR	-	3:1	-	$V_{CE} = 28\text{V}$, $P_{out} = 1.0\text{W}$, $F = 2.3\text{GHz}$

TEST FIXTURE IMPEDANCES

F (GHz)	Z_{IN} (Ω)	Z_{LOAD} (Ω)
2.30	$12.5-j26.0$	$3.7+j10.4$



TEST FIXTURE DIMENSIONS



TEST FIXTURE ASSEMBLY

